



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



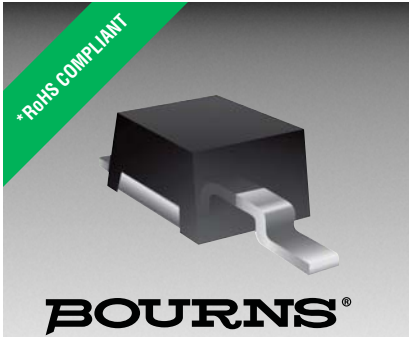
## Contact us

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## Features

- RoHS compliant\*
- Low profile
- Surface mount
- Very low forward voltage drop

## Applications

- Cellular phones
- PDAs
- Desktop PCs and notebooks
- Digital cameras
- MP3 players

# CD216A-B120L~B140 MITE Chip Diode

## General Information

The markets of portable communications, computing and video equipment are challenging the semiconductor industry to develop increasingly smaller electronic components.

Bourns offers Schottky Rectifier Diodes for rectification applications in compact DO-216AA size chip package formats, which offer PCB real estate savings and are considerably smaller than competitive parts. The Schottky Barrier Rectifier Diodes offer a forward current of 1 A with a choice of repetitive peak reverse voltage of 20 V up to 40 V.

Bourns® Chip Diodes conform to JEDEC standards, are easy to handle with standard pick and place equipment and their flat configuration minimizes roll away.

## Electrical Characteristics (@ T<sub>A</sub> = 25 °C Unless Otherwise Noted)

Parameter	Symbol	CD216-				Unit
		B120L	B120R	B130L	B140	
Forward Voltage (Max.) (I <sub>F</sub> = 1 A)	V <sub>F</sub>	0.45	0.53	0.38	0.55	V
Typical Junction Capacitance**	C <sub>T</sub>	90	75	70	60	pF
Reverse Current (Max.) (@ Rated V <sub>R</sub> )	I <sub>R</sub>	400	10	410	500	μA

\*\*Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

## Absolute Ratings (@ T<sub>A</sub> = 25 °C Unless Otherwise Noted)

Parameter	Symbol	CD216-				Unit
		B120L	B120R	B130L	B140	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	20	20	30	40	V
DC Blocking Voltage	V <sub>DC</sub>	20	20	30	40	V
RMS Voltage	V <sub>RMS</sub>	14	14	21	28	V
Average Forward Current @ T <sub>L</sub> = 130 °C	I <sub>O</sub>	1				A
Peak Forward Surge Current***	I <sub>FSM</sub>	50	50	50	40	A
Max. Instantaneous Forward Voltage**** @ I <sub>F</sub> = 0.1 A @ I <sub>F</sub> = 1.0 A @ I <sub>F</sub> = 2.0 A @ I <sub>F</sub> = 3.0 A	V <sub>F</sub>	0.34 0.45 0.65	0.455 0.53 0.595	0.30 0.38 0.52	0.36 0.55 0.85	V
Max. Instantaneous Reverse Current @ V <sub>R</sub> = 40 V @ V <sub>R</sub> = 30 V @ V <sub>R</sub> = 20 V @ V <sub>R</sub> = 10 V @ V <sub>R</sub> = 5 V	I <sub>R</sub>	0.4 0.1	0.0100 0.0010 0.0005	0.41 0.13 0.05	0.50 0.15	mA
Thermal Resistance Junction to Lead (Anode) Junction to Tab (Cathode) Junction to Ambient	R <sub>θJL</sub> R <sub>θJTAB</sub> R <sub>θJA</sub>	35 20 250				°C/W
Storage Temperature	T <sub>STG</sub>	-55 to +150				°C
Junction Temperature	T <sub>J</sub>	-55 to +125				°C

\*\*\*Surge Current 8.3 ms single phase, half sine wave, 60 Hz (JEDEC Method).

\*\*\*\*Pulse Test; Pulse Width = 300 μS, Duty Cycle = 2 %.

\*RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011.

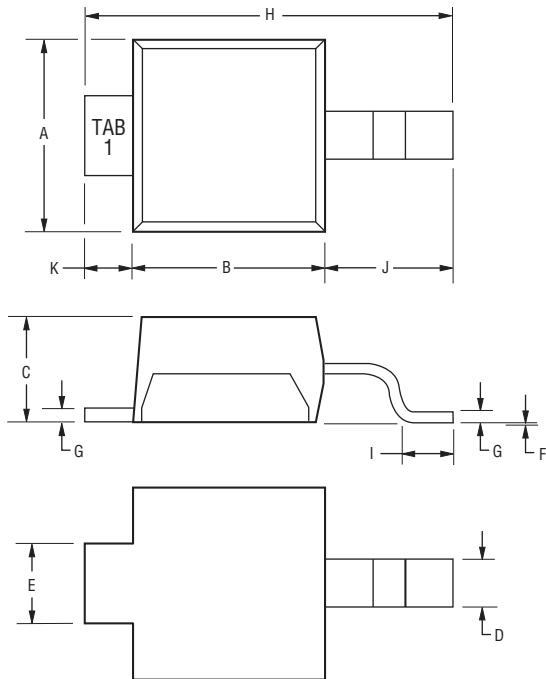
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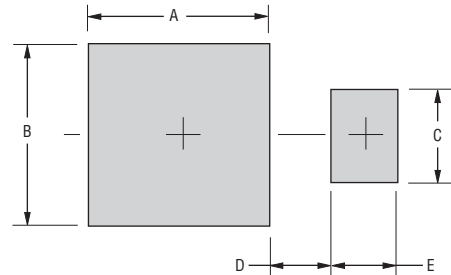
## Product Dimensions



Dimension	DO-216AA
A	$\frac{1.75 - 2.05}{(0.069 - 0.081)}$
B	$\frac{1.80 - 2.20}{(0.071 - 0.087)}$
C	$\frac{0.95 - 1.15}{(0.037 - 0.045)}$
D	$\frac{0.42 - 0.68}{(0.017 - 0.027)}$
E	$\frac{0.70 - 1.00}{(0.028 - 0.039)}$
F	$\frac{0.05 - 0.10}{(0.002 - 0.004)}$
G	$\frac{0.10 - 0.25}{(0.004 - 0.010)}$
H	$\frac{3.65 - 3.95}{(0.144 - 0.156)}$
I	$\frac{0.40 - 0.70}{(0.016 - 0.028)}$
J	$\frac{1.10 - 1.50}{(0.043 - 0.059)}$
K	$\frac{0.20 - 0.80}{(0.008 - 0.060)}$

DIMENSIONS:  $\frac{\text{MM}}{(\text{INCHES})}$

## Recommended Pad Layout



Dimension	DO-216AA
A	$\frac{2.67}{(0.105)}$
B	$\frac{2.54}{(0.100)}$
C	$\frac{1.27}{(0.050)}$
D	$\frac{0.625}{(0.025)}$
E	$\frac{0.762}{(0.030)}$

## Physical Specifications

Case ..... JEDEC 20-216AA Molded plastic  
 Polarity..... Cathode designated by TAB 1  
 Weight ..... Approximately 0.016 grams  
 Mounting Position..... One way

## Typical Part Marking

CD216A-B120L ..... B2L  
 CD216A-B120R ..... B2E  
 CD216A-B130L ..... B3L  
 CD216A-B140 ..... B4S

## How to Order

**CD 216A - B 1 20 L LF**

Common Code \_\_\_\_\_  
 Chip Diode \_\_\_\_\_  
 Package \_\_\_\_\_  
 • 216A = DO-216AA  
 Model \_\_\_\_\_  
 B = Schottky Barrier Series  
 Average Forward Current (IO) Code \_\_\_\_\_  
 1 = 1 A (Code x 1000 mA = Average Forward Current)  
 Reverse Voltage (VR) Code \_\_\_\_\_  
 20 = 20 V  
 30 = 30 V  
 40 = 40 V  
 Forward Voltage Suffix \_\_\_\_\_  
 L = Low Forward Voltage Vf (CD216-B120L, CD216-B130L)  
 R = Low Leakage Current IR (CD216-B120R)  
 Terminations \_\_\_\_\_  
 LF = 100 % Sn (RoHS Compliant)

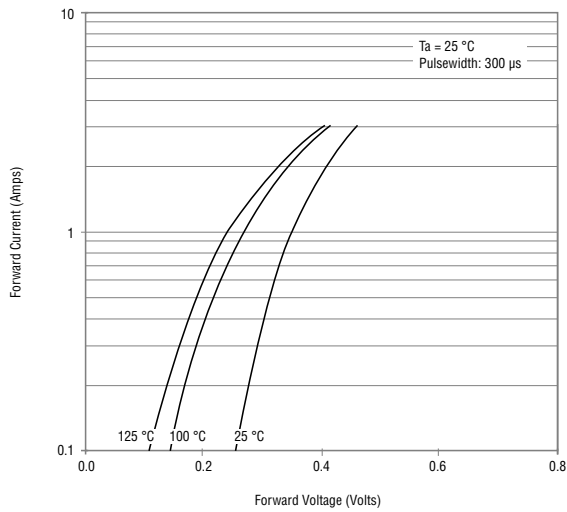
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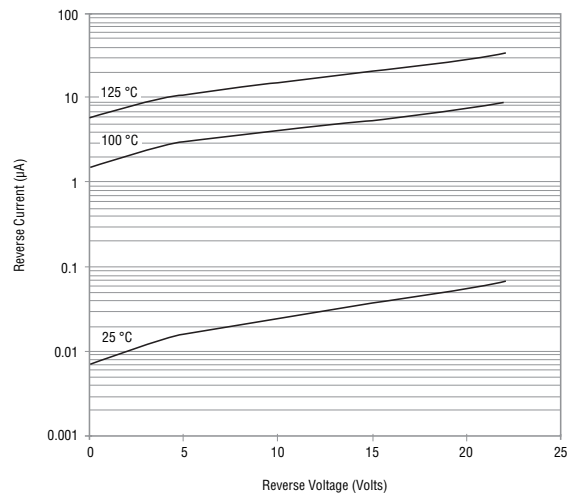
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## Rating & Characteristic Curves: CD216A-B120L

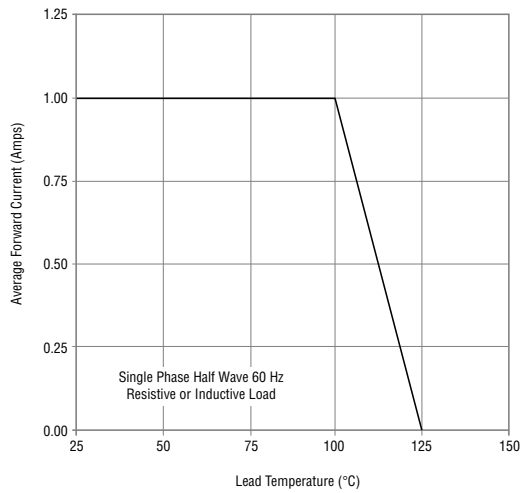
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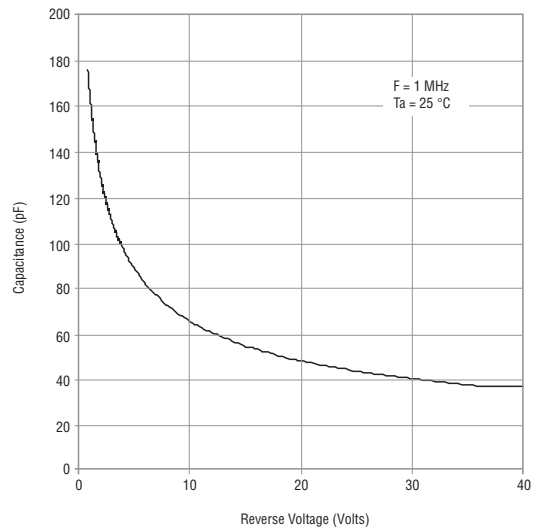
### Reverse Characteristics



### Derating Curve



### Capacitance Between Terminals



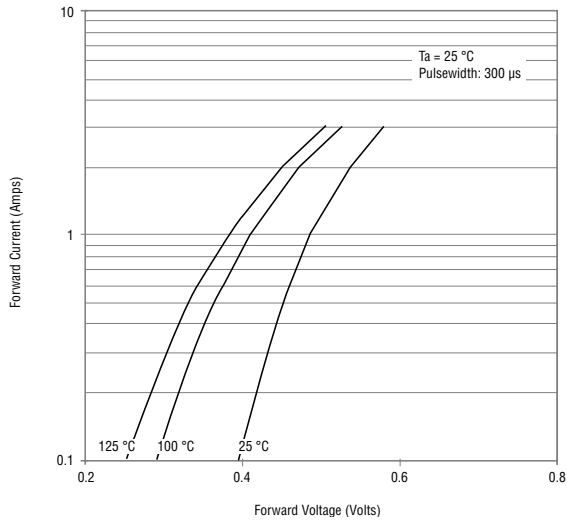
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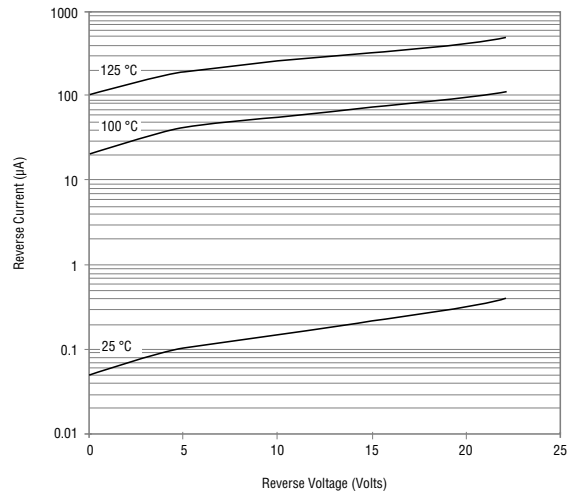
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## Rating & Characteristic Curves: CD216A-B120R

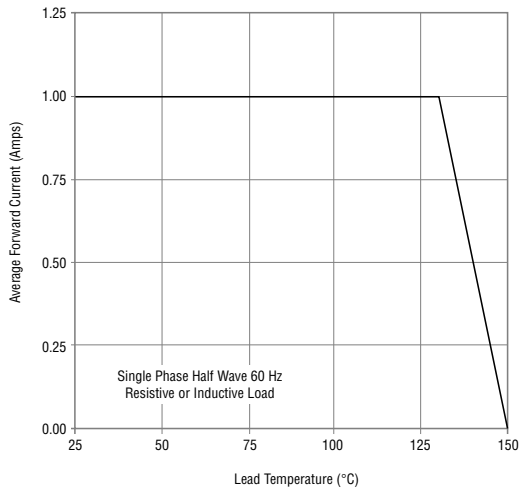
### Forward Characteristics



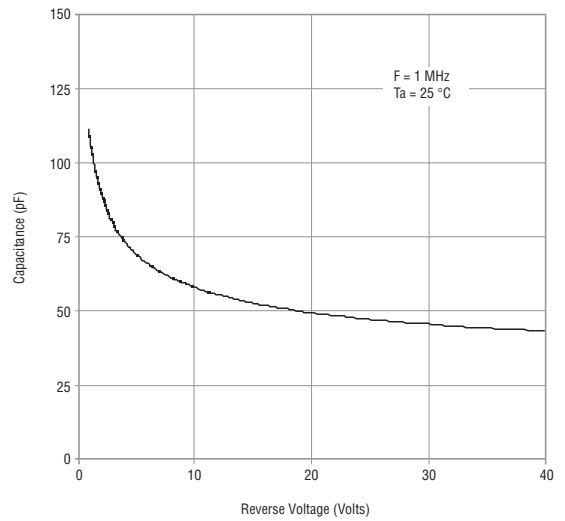
### Reverse Characteristics



### Derating Curve



### Capacitance Between Terminals



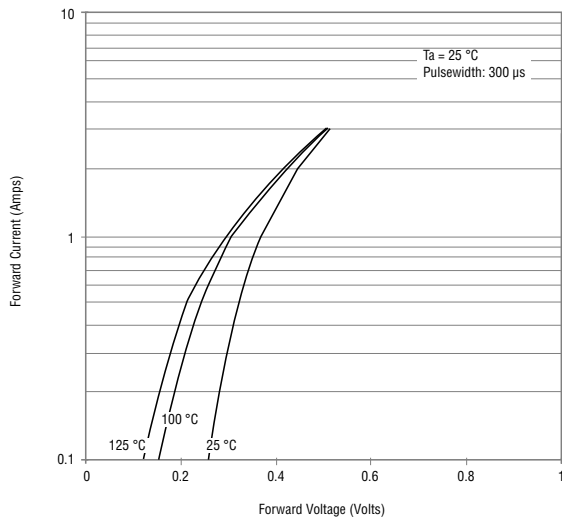
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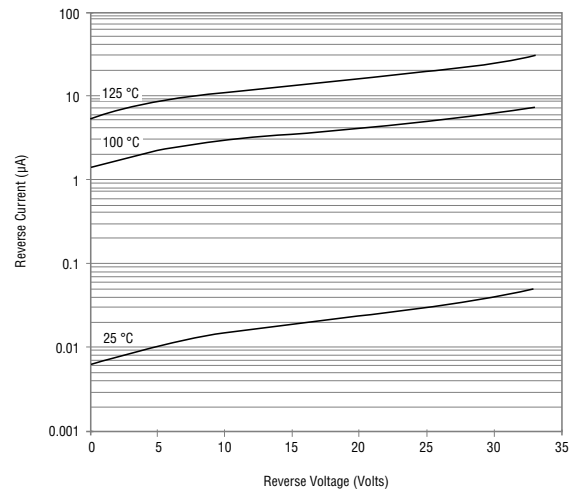
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## Rating & Characteristic Curves: CD216A-B130L

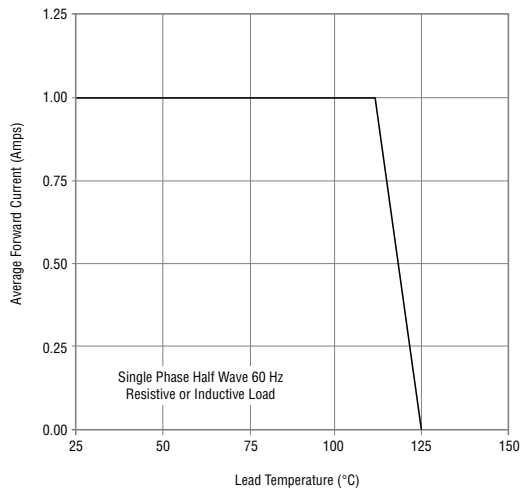
### Forward Characteristics



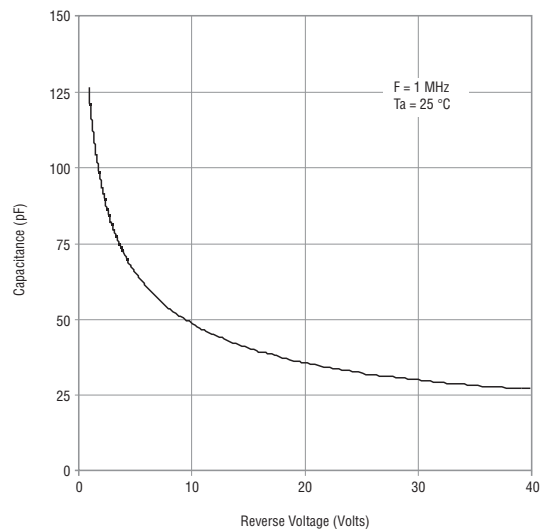
### Reverse Characteristics



### Derating Curve



### Capacitance Between Terminals



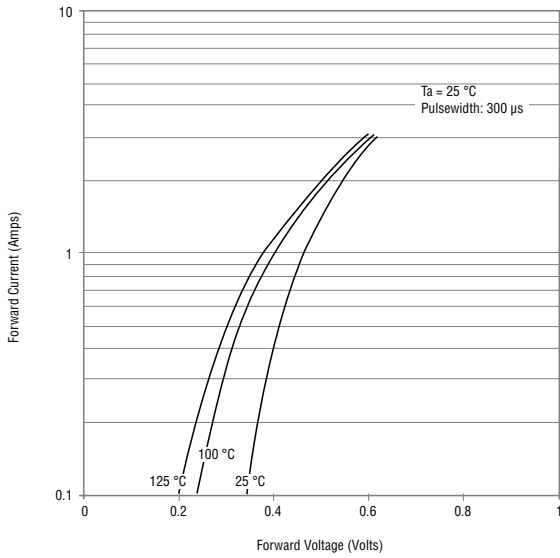
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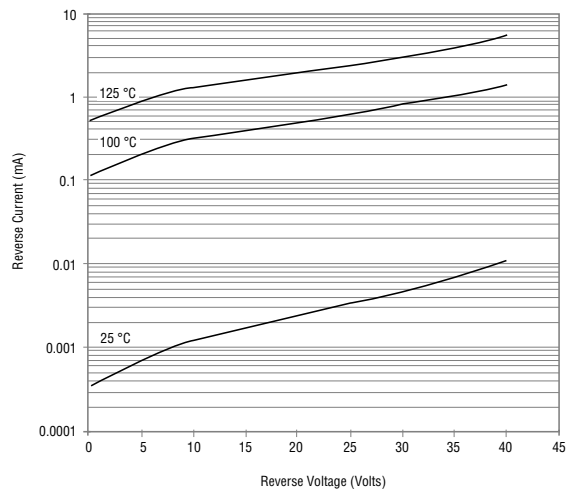
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## Rating & Characteristic Curves: CD216A-B140

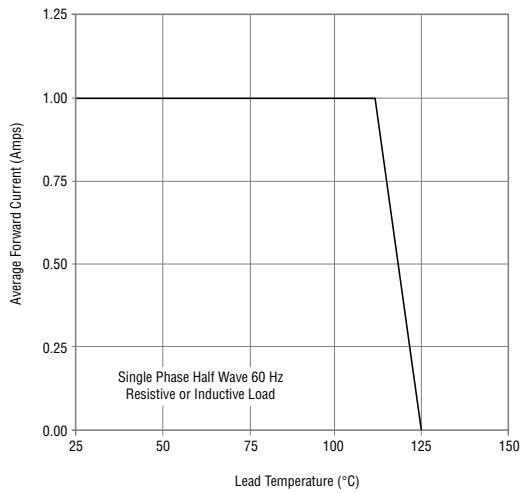
### Forward Characteristics



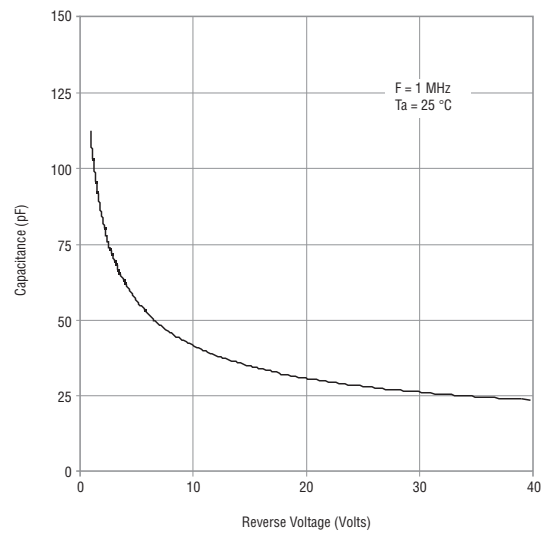
### Reverse Characteristics



### Derating Curve



### Capacitance Between Terminals



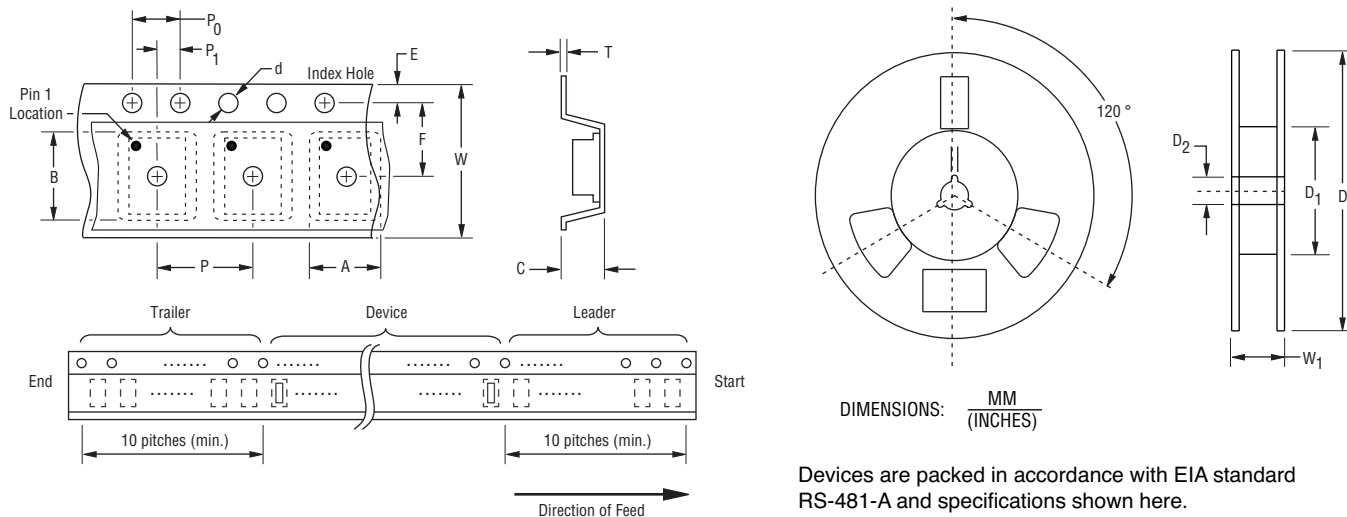
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# CD216A-B120L~B140 MITE Chip Diode

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## Packaging Information

The product is dispensed in tape and reel format (see diagram below).



Item	Symbol	DO-216AA
Carrier Width	A	$\frac{2.90 \pm 0.10}{(0.114 \pm 0.004)}$
Carrier Length	B	$\frac{5.30 \pm 0.10}{(0.209 \pm 0.004)}$
Carrier Depth	C	$\frac{1.37 \pm 0.10}{(0.054 \pm 0.004)}$
Sprocket Hole	d	$\frac{1.55 \pm 0.05}{(0.061 \pm 0.002)}$
Reel Outside Diameter	D	$\frac{178}{(7.008)}$
Reel Inner Diameter	D <sub>1</sub>	$\frac{75.0}{(2.953)}$ MIN.
Feed Hole Diameter	D <sub>2</sub>	$\frac{13.0 \pm 0.20}{(0.512 \pm 0.008)}$
Sprocket Hole Position	E	$\frac{1.75 \pm 0.10}{(0.069 \pm 0.004)}$
Punch Hole Position	F	$\frac{5.50 \pm 0.05}{(0.217 \pm 0.002)}$
Punch Hole Pitch	P	$\frac{4.00 \pm 0.10}{(0.157 \pm 0.004)}$
Sprocket Hole Pitch	P <sub>0</sub>	$\frac{4.00 \pm 0.10}{(0.157 \pm 0.004)}$
Embossment Center	P <sub>1</sub>	$\frac{2.00 \pm 0.05}{(0.079 \pm 0.002)}$
Overall Tape Thickness	T	$\frac{0.40 \pm 0.10}{(0.016 \pm 0.004)}$
Tape Width	W	$\frac{12.00 \pm 0.20}{(0.472 \pm 0.008)}$
Reel Width	W <sub>1</sub>	$\frac{18.4}{(0.724)}$ MAX.
Quantity per Reel	--	3,000

**BOURNS®**

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